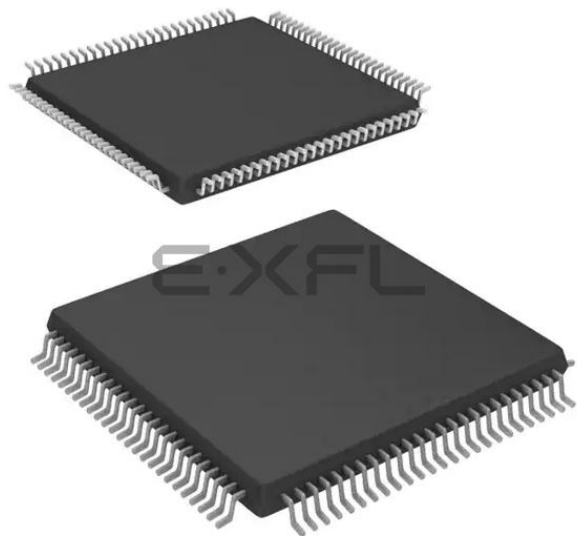




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

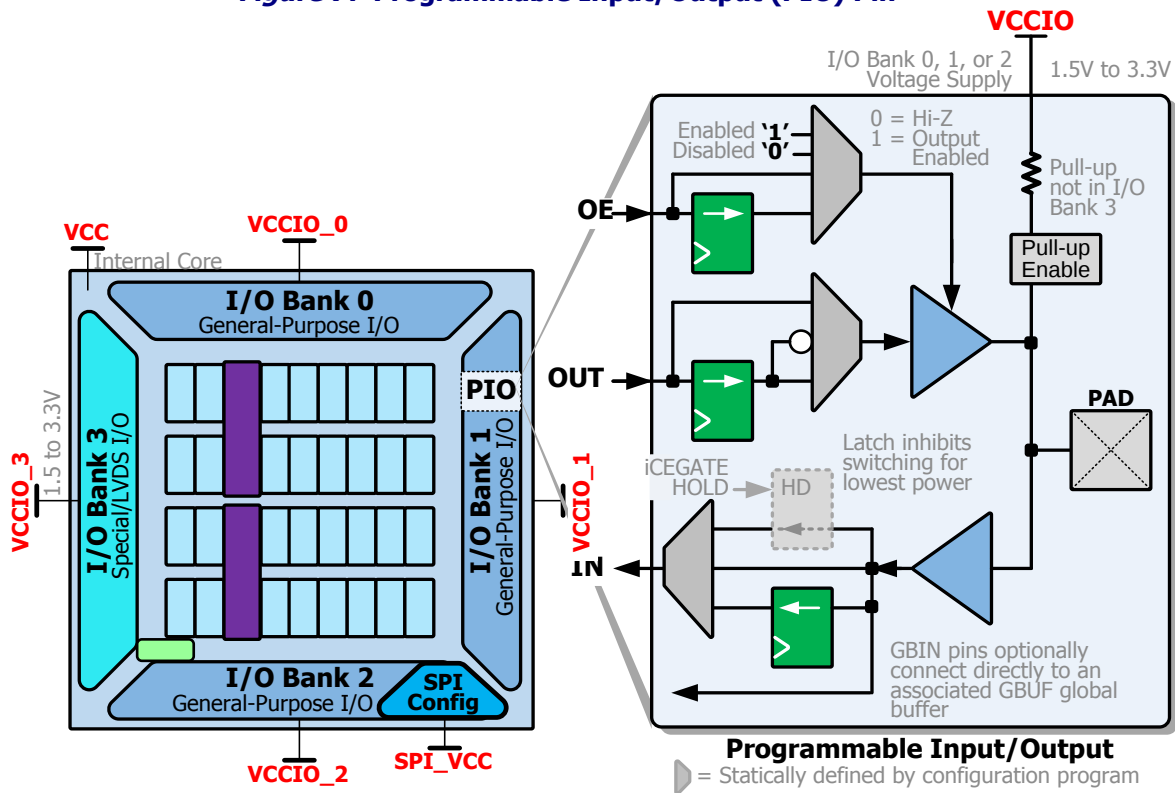
Product Status	Obsolete
Number of LABs/CLBs	440
Number of Logic Elements/Cells	3520
Total RAM Bits	81920
Number of I/O	72
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/ice65l04f-lvq100c

Programmable Input/Output Block (PIO)

Programmable Input/Output (PIO) blocks surround the periphery of the device and connect external components to the Programmable Logic Blocks (PLBs) and RAM4K blocks via programmable interconnect. Individual PIO pins are grouped into one of four I/O banks, as shown in Figure 7. I/O Bank 3 has additional capabilities, including LVDS differential I/O and the ability to interface to Mobile DDR memories.

Figure 7 also shows the logic within a PIO pin. When used in an application, a PIO pin becomes a signal input, an output, or a bidirectional I/O pin with a separate direction control input.

Figure 7: Programmable Input/Output (PIO) Pin



I/O Banks

PIO blocks are organized into four separate I/O banks, each with its own voltage supply input, as shown in Table 5. The voltage applied to the VCCIO pin on a bank defines the I/O standard used within the bank. Table 50 and Table 51 describe the I/O drive capabilities and switching thresholds by I/O standard. On iCE65L04 and iCE65L08 devices, I/O Bank 3, along the left edge of the die, is different than the others and supports specialized I/O standards.

I/O Bank Voltage Supply Inputs Support Different I/O Standards

Because each I/O bank has its own voltage supply, iCE65 components become the ideal bridging device between different interface standards. For example, the iCE65 device allows a 1.8V-only processor to interface cleanly with a 3.3V bus interface. The iCE65 device replaces external voltage translators.

Table 5: Supported Voltages by I/O Bank

Bank	Device Edge	Supply Input	3.3V	2.5V	1.8V	1.5V
0	Top	VCCIO_0	Yes	Yes	Yes	Outputs only
1	Right	VCCIO_1	Yes	Yes	Yes	Outputs only
2	Bottom	VCCIO_2	Yes	Yes	Yes	Outputs only
3	Left	VCCIO_3	Yes	Yes	Yes	iCE65L01: Outputs only iCE65L04/08: Yes
SPI	Bottom Right	SPI_VCC	Yes	Yes	Yes	No

If not connected to an external SPI PROM, the four pins associated with the [SPI Master Configuration Interface](#) can be used as PIO pins, supplied by the SPI_VCC input, essentially forming a fifth “mini” I/O bank. If using an SPI Flash PROM, then connect SPI_VCC to 3.3V.

I/O Banks 0, 1, 2, SPI and Bank 3 of iCE65L01

[Table 6](#) highlights the available I/O standards when using an iCE65 device, indicating the drive current options, and in which bank(s) the standard is supported. I/O Banks 0, 1, 2 and SPI interface support the same standards. I/O Bank 3 has additional capabilities in iCE65L04 and iCE65L08, including support for MDDR memory standards and LVDS differential I/O.

Table 6: I/O Standards for I/O Banks 0, 1, 2, SPI Interface Bank, and Bank 3 of iCE65L01

I/O Standard	Supply Voltage	Drive Current (mA)	Attribute Name
5V Input Tolerance	3.3V	N/A	N/A
LVCN0533	3.3V	±11	SB_LVCN05
LVCN0525	2.5V	±8	
LVCN0518	1.8V	±5	
LVCN0515 outputs	1.5V	±4	

IBIS Models for I/O Banks 0, 1, 2 and the SPI Bank

The IBIS (I/O Buffer Information Specification) file that describes the output buffers used in I/O Banks 0, 1, 2, SPI Bank and Bank 3 of iCE65L01 is available from the following link.

- [IBIS Models for I/O Banks 0, 1, 2, SPI Bank and Bank 3 of iCE65L01](#)

I/O Bank 3 of iCE65L04 and iCE65L08

I/O Bank 3, located along the left edge of the die, has additional special I/O capabilities to support memory components and differential I/O signaling (LVDS). [Table 7](#) lists the various I/O standards supported by I/O Bank 3. The SSTL2 and SSTL18 I/O standards require the VREF voltage reference input pin which is only available on the CB284 package. Also see [Table 5I](#) for electrical characteristics.

Table 7: I/O Standards for I/O Bank 3 Only of iCE65L04 and iCE65L08

I/O Standard	Supply Voltage	VREF Pin (CB284 or DiePlus) Required?	Target Drive Current (mA)	Attribute Name
LVCN0533	3.3V	No	±8	SB_LVCN0533_8
LVCN0525	2.5V	No	±16	SB_LVCN0525_16
			±12	SB_LVCN0525_12
			±8	SB_LVCN0525_8
			±4	SB_LVCN0525_4
LVCN0518	1.8V	No	±10	SB_LVCN0518_10
			±8	SB_LVCN0518_8
			±4	SB_LVCN0518_4
			±2	SB_LVCN0518_2
LVCN0515	1.5V	No	±4	SB_LVCN0515_4
			±2	SB_LVCN0515_2
SSTL2_II	2.5V	Yes	±16.2	SB_SSTL2_CLASS_2
SSTL2_I			±8.1	SB_SSTL2_CLASS_1
SSTL18_II	1.8V	Yes	±13.4	SB_SSTL18_FULL
SSTL18_I			±6.7	SB_SSTL18_HALF
MDDR	1.8V	No	±10	SB_MDDR10
			±8	SB_MDDR8
			±4	SB_MDDR4
			±2	SB_MDDR2
LVDS	2.5V	No	N/A	SB_LVDS_INPUT

Table 12 and Table 13 list the connections between a specific global buffer and the inputs on a Programmable I/O (PIO) pair. Although there is no direct connection between a global buffer and a PIO output, such a connection is possible by first connecting through a PLB LUT4 function. Again, all global buffers optionally drive all clock inputs. However, even-numbered global buffers optionally drive the clock-enable input on a PIO pair.



The PIO clock enable connect is different between the iCE65L01/iCE65L04 and iCE65L08.

Table 12: iCE65L01 & iCE65L04: Global Buffer (GBUF) Connections to Programmable I/O (PIO) Pair

Global Buffer	Output Connections	Input Clock	Output Clock	Clock Enable
GBUF0	No (connect through PLB LUT)	Yes	Yes	No
GBUF1		Yes	Yes	Yes
GBUF2		Yes	Yes	No
GBUF3		Yes	Yes	Yes
GBUF4		Yes	Yes	No
GBUF5		Yes	Yes	Yes
GBUF6		Yes	Yes	No
GBUF7		Yes	Yes	Yes

Table 13: iCE64L08: Global Buffer (GBUF) Connections to Programmable I/O (PIO) Pair

Global Buffer	Output Connections	Input Clock	Output Clock	Clock Enable
GBUF0	No (connect through PLB LUT)	Yes	Yes	Yes
GBUF1		Yes	Yes	No
GBUF2		Yes	Yes	Yes
GBUF3		Yes	Yes	No
GBUF4		Yes	Yes	Yes
GBUF5		Yes	Yes	No
GBUF6		Yes	Yes	Yes
GBUF7		Yes	Yes	No

Global Buffer Inputs

The iCE65 component has eight specialized GBIN/PIO pins that are optionally direct inputs to the global buffers, offering the best overall clock characteristics. As shown in Figure 15, each GBIN/PIO pin is a full-featured I/O pin but also provides a direct connection to its associated global buffer. The direct connection to the global buffer bypasses the iCEgate input-blocking latch and other PIO input logic. These special PIO pins are allocated two to an I/O Bank, a total of eight. These pins are labeled GBIN0 through GBIN7, as shown in Figure 14 and the pin locations for each GBIN input appear in Table 14.

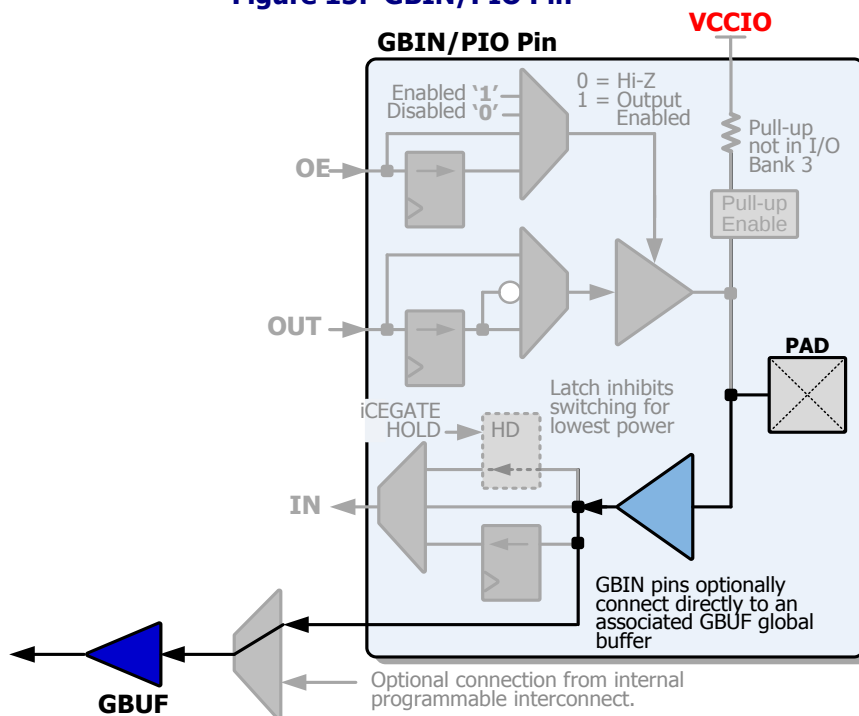
Table 14: Global Buffer Input Ball/Pin Number by Package

Global Buffer Input (GBIN)	I/O Bank	VQ100	CB132	'L04 CB196	'L08 CB196	CB284
GBIN0	0	90	A6	A7	A7	E10
GBIN1		89	A7	E7	E7	E11
GBIN2	1	63	G14	F10	F10	L18
GBIN3		62	F14	G12	G12	K18
GBIN4	2	34	P8	L7	N8	V12
GBIN5		33	P7	P5	M7	V11
GBIN6	3	15	H1	H1	H1	M5
GBIN7		13	G1	G1	H3	L5



Note the clock differences between the iCE65L04 and iCE65L08 in the CB196 package.

Figure 15: GBIN/PIO Pin



Differential Global Buffer Input

All eight global buffer inputs support single-ended I/O standards such as LVC MOS. Global buffer GBUF7 in I/O Bank 3 also provides an optional direct SubLVDS, LVDS, or LVPECL differential clock input, as shown in Figure 16. The GBIN7 and its associated differential I/O pad accept a differential clock signal. A 100 Ω termination resistor is required across the two pads. Optionally, swap the outputs from the LVDS or LVPECL clock driver to invert the clock as it enters the iCE65 device.

Figure 16: LVDS or LVPECL Clock Input

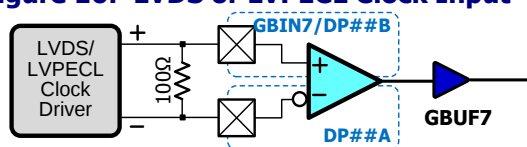


Table 15 lists the pin or ball numbers for the differential global buffer input by package style. Although this differential input is the only one that connects directly to a global buffer, other differential inputs can connect to a global buffer using general-purpose interconnect, with slightly more signal delay.

Table 15: Differential Global Buffer Input Ball/Pin Number by Package

Differential Global Buffer Input (GBIN)	I/O Bank	VQ100	CB132	'L04 CB196	'L08 CB196	CB284
GBIN7/DPxxB	3	13	N/A	G1	H3	L5
DPxxA		12	N/A	G2	H4	L3



The differential global buffer input is not available for iCE65 devices in the CB132 package. This restriction is an artifact of the pin compatibility between the CB132 and CB284 package.

Note the clock differences between the iCE65L04 and iCE65L08 in the CB196 package.

- For lowest possible power consumption after configuration, the PROM should also support the **0xB9** Deep Power Down command and the **0xAB** Release from Deep Power-down Command (see [Figure 24](#) and [Figure 26](#)). The low-power mode is optional.
- The PROM must be ready to accept commands 10 μ s after meeting its power-on conditions. In the PROM data sheet, this may be specified as t_{VSL} or t_{VCSL} . It is possible to use slower PROMs by holding the CRESET_B input Low until the PROM is ready, then releasing CRESET_B, either under program control or using an external power-on reset circuit.

The Lattice iCEman65 development board and associated programming software uses an ST Micro/Numonyx M25Pxx SPI serial Flash PROM.

SPI PROM Size Requirements

[Table 27](#) lists the minimum SPI PROM size required to configure an iCE65 device. Larger PROM sizes are allowed, but not required unless the end application uses the additional space. SPI serial PROM sizes are specified in bits. For each device size, the table shows the required minimum PROM size for “Logic Only” (no BRAM initialization) and “Logic + RAM4K” (RAM4K blocks pre-initialized). Furthermore, the table shows the PROM size for varying numbers of configuration images. Most applications will use a single image. Applications that use the Cold Boot or Warm Boot features may use more than one image.

Table 27: Smallest SPI PROM Size (bits), by Device, by Number of Images

Device	1 Image		2 Images		3 Images		4 Images	
	Logic Only	Logic + RAM4K	Logic Only	Logic + RAM4K	Logic Only	Logic + RAM4K	Logic Only	Logic + RAM4K
iCE65L01	256K	256K	512K	512K	1M	1M	1M	1M
iCE65L04	512K	1M	1M	2M	2M	2M	2M	4M
iCE65L08	1M	2M	2M	4M	4M	4M	4M	8M

Enabling SPI Configuration Interface

To enable the SPI configuration mode, the SPI_SS_B pin must be allowed to float High. The SPI_SS_B pin has an internal pull-up resistor. If SPI_SS_B is Low, then the iCE65 component defaults to the SPI Slave configuration mode.

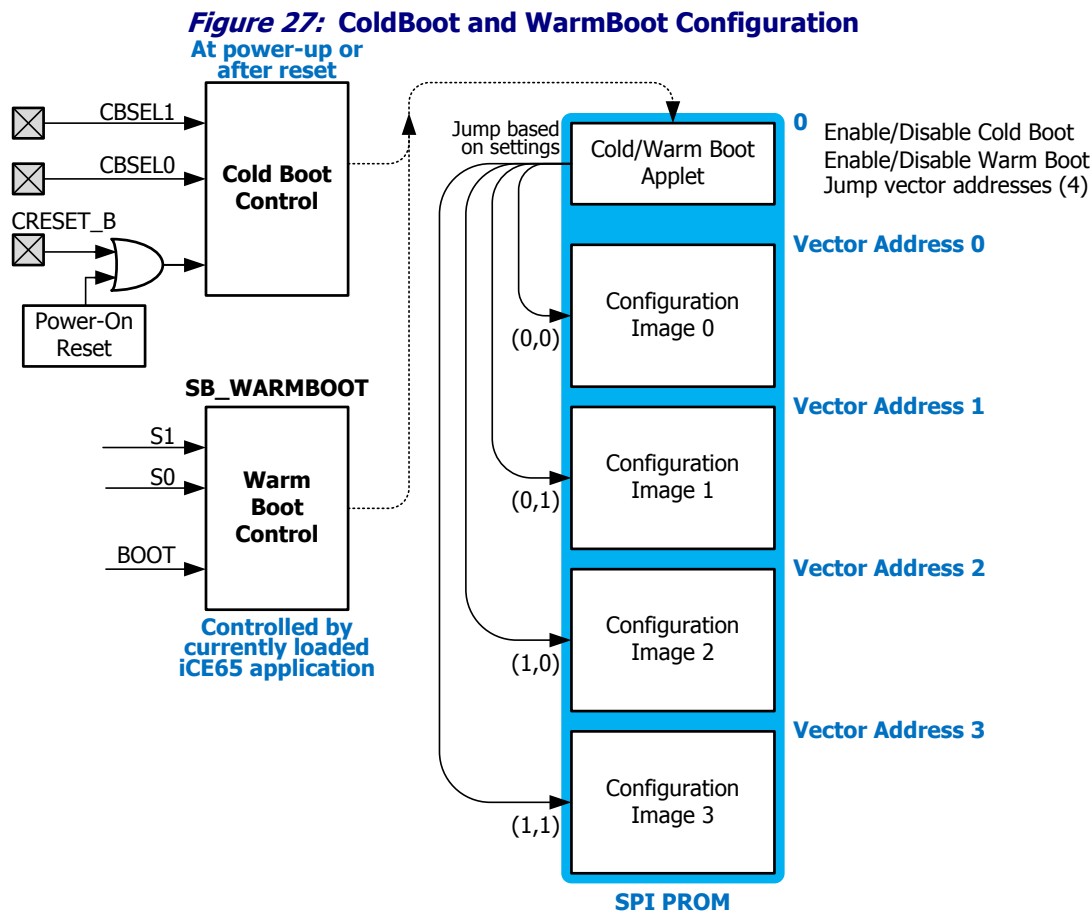
SPI Master Configuration Process

The iCE65 SPI Master Configuration Interface supports a variety of modern, high-density, low-cost SPI serial Flash PROMs. Most modern SPI PROMs include a power-saving Deep Power-down mode. The iCE65 component exploits this mode for additional system power savings.

The iCE65 SPI interface starts by driving [SPI_SS_B](#) Low, and then sends a Release from Power-down command to the SPI PROM, hexadecimal command code **0xAB**. [Figure 24](#) provides an example waveform. This initial command wakes up the SPI PROM if it is already in Deep Power-down mode. If the PROM is not in Deep Power-down mode, the extra command has no adverse affect other than that it requires a few additional microseconds during the configuration process. The iCE65 device transmits data on the [SPI_SO](#) output, on the falling edge of the [SPI_SCK](#) output. The SPI PROM does not provide any data to the iCE65 device’s [SPI_SI](#) input. After sending the last command bit, the iCE65 device de-asserts SPI_SS_B High, completing the command. The iCE65 device then waits a minimum of 10 μ s before sending the next SPI PROM command.

Cold Boot Configuration Option

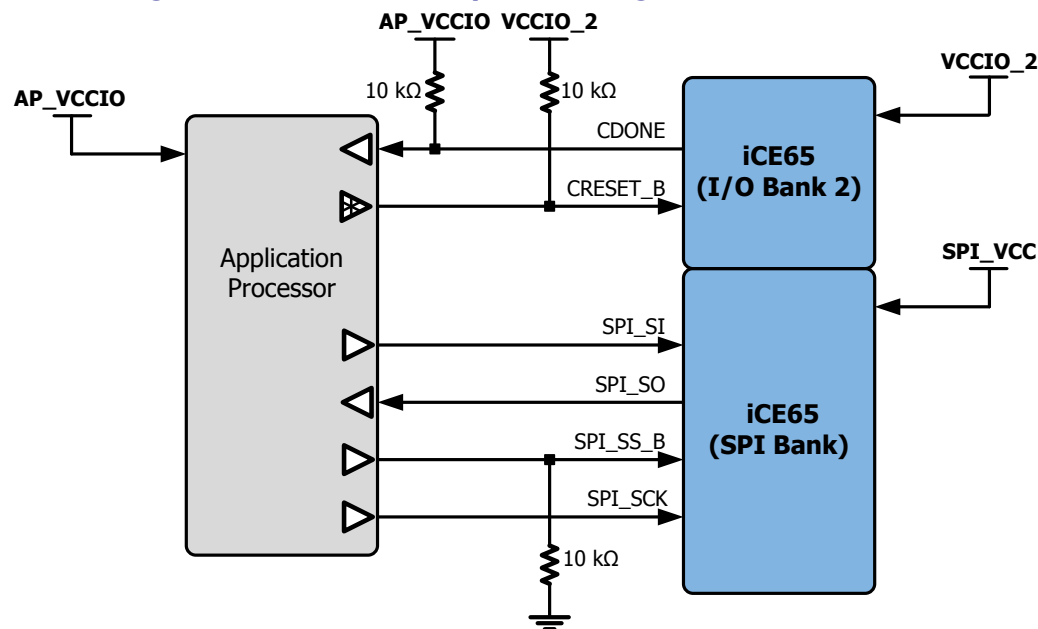
By default, the iCE65 FPGA is programmed with a single configuration image, either from internal NVCM memory, from an external SPI Flash PROM, or externally from a processor or microcontroller.



When self loading from NVCM or from an SPI Flash PROM, there is an additional configuration option called Cold Boot mode. When this option is enabled in the configuration bitstream, the iCE65 FPGA boots normally from power-on or a master reset (CRESET_B = Low pulse), but monitors the value on two PIO pins that are borrowed during configuration, as shown in Figure 27. These pins, labeled PIO2/CBSEL0 and PIO2/CBSEL1, tell the FPGA which of the four possible SPI configurations to load into the device. Table 30 provides the pin or ball locations for these pins.

- Load from initial location, either from NVCM or from address 0 in SPI Flash PROM. For Cold Boot or Warm Boot applications, the initial configuration image contains the cold boot/warm boot applet.
- Check if Cold Boot configuration feature is enabled in the bitstream.
 - ◆ If not enabled, FPGA configures normally.
 - ◆ If Cold Boot is enabled, then the FPGA reads the logic values on pins CBSEL[1:0]. The FPGA uses the value as a vector and then reads from the indicated vector address.
 - ◆ At the selected CBSEL[1:0] vector address, there is a starting address for the selected configuration image.
 - For SPI Flash PROMs, the new address is a 24-bit start address in Flash.
 - If the selected bitstream is in NVCM, then the address points to the internal NVCM.
- Using the new start address, the FPGA restarts reading configuration memory from the new location.

Figure 28: iCE65 SPI Peripheral Configuration Interface



The SPI control signals are defined in [Table 25](#).

Table 29: SPI Peripheral Configuration Interface Pins (SPI_SS_B Low when CRESET_B Released)

Signal Name	Direction	iCE65 I/O Supply	Description
CDONE	AP ← iCE65	VCCIO_2	Configuration Done output from iCE65. Connect to a 10kΩ pull-up resistor to the application processor I/O voltage, AP_VCC.
CRESET_B	AP → iCE65	VCCIO_2	Configuration Reset input on iCE65. Typically driven by AP using an open-drain driver, which also requires a 10kΩ pull-up resistor to VCCIO_2.
SPI_VCC	Supply	SPI_VCC	SPI Flash PROM voltage supply input.
SPI_SI	AP → iCE65	SPI_VCC	SPI Serial Input to the iCE65 FPGA, driven by the application processor.
SPI_SO	AP ← iCE65	SPI_VCC	SPI Serial Output from CE65 device to the application processor. Not actually used during SPI peripheral mode configuration but required if the SPI interface is also used to program the NVCM.
SPI_SS_B	AP → iCE65	SPI_VCC	SPI Slave Select output from the application processor. Active Low. Optionally hold Low prior to configuration using a 10kΩ pull-down resistor to ground.
SPI_SCK	AP → iCE65	SPI_VCC	SPI Slave Clock output from the application processor.

After configuration, the SPI port pins are available to the user-application as additional PIO pins, supplied by the SPI_VCC input voltage, essentially providing a fifth “mini” I/O bank.

Enabling SPI Configuration Interface

The optional 10 kΩ pull-down resistor on the SPI_SS_B signal ensures that the iCE65 FPGA powers up in the SPI peripheral mode. Optionally, the application processor drives the SPI_SS_B pin Low when CRESET_B is released, forcing the iCE65 FPGA into SPI peripheral mode.

SPI Peripheral Configuration Process

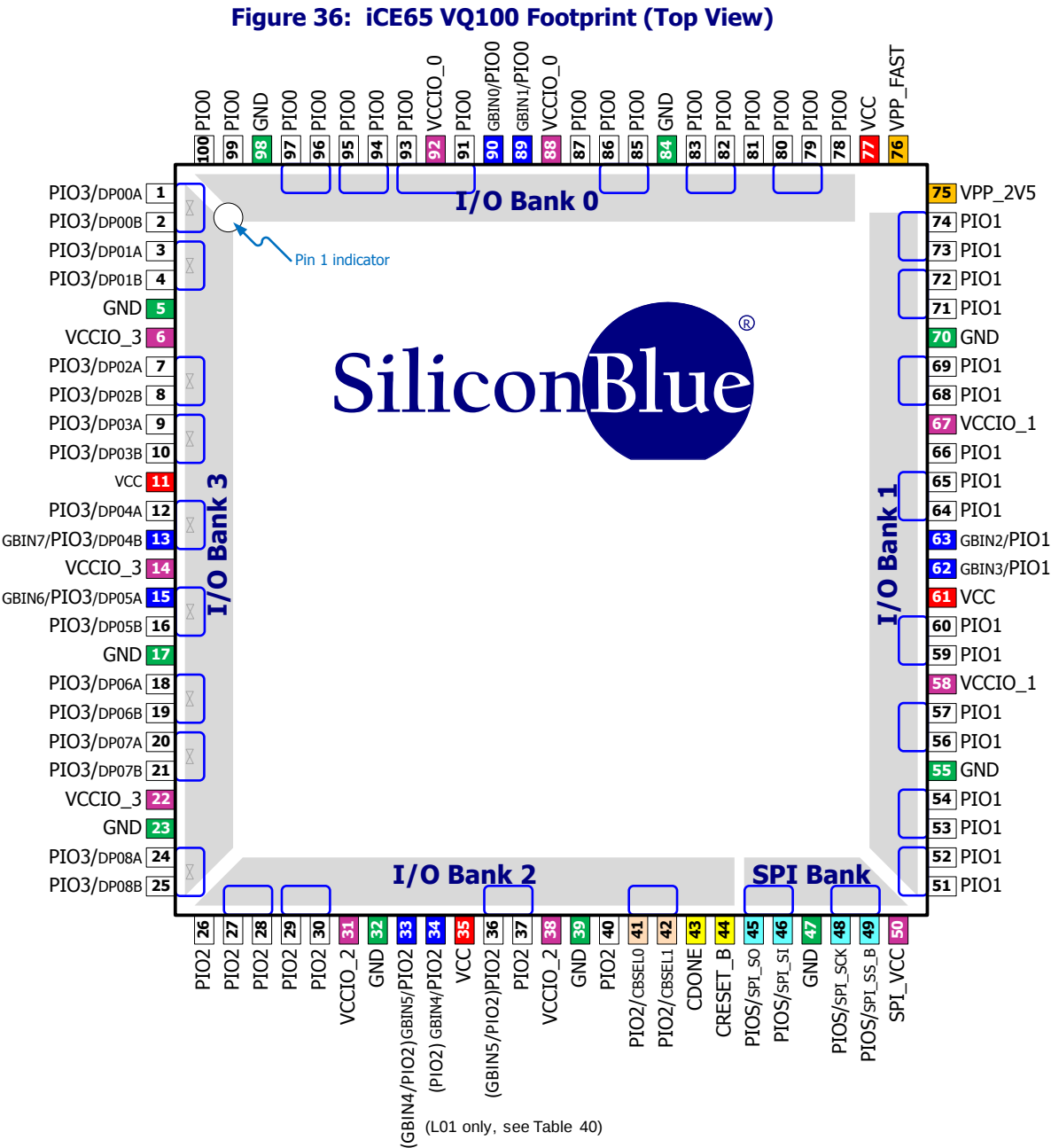
[Figure 29](#) illustrates the interface timing for the SPI peripheral mode and [Figure 30](#) outlines the resulting configuration process. The actual timing specifications appear in [Table 60](#). The application processor (AP) begins by driving the iCE65 CRESET_B pin Low, resetting the iCE65 FPGA. Similarly, the AP holds the iCE65’s SPI_SS_B pin Low. The AP must hold the CRESET_B pin Low for at least 200 ns. Ultimately, the AP either releases the CRESET_B pin and allows it to float High via the 10 kΩ pull-up resistor to VCCIO_2 or drives CRESET_B High. The iCE65 FPGA enters SPI peripheral mode when the CRESET_B pin returns High while the SPI_SS_B pin is Low.

VQ100 Very-thin Quad Flat Package

The VQ100 package is a very-thin quad-flat package with 0.5 mm lead pitch. The iCE65L01 and iCE65L04 devices are available in this package.

Footprint Diagram

Figure 36 shows the footprint diagram for the 100-lead very-thin quad-flat package (VQ100). See Table 40 for a complete, detailed pinout for the 100-lead very-thin quad-flat package. The signal pins are also grouped into the four I/O Banks and the SPI interface.



Pinout Table

Table 39 provides a detailed pinout table for the VQ100 package. Pins are generally arranged by I/O bank, then by pin function. The table also highlights the differential I/O pairs in I/O Bank 3. The VQ100 package has no JTAG pins.

iCE65 Ultra Low-Power mobileFPGA™ Family

Pin Function	Pin Number	Type	Bank
PIO2	28	PIO	2
PIO2	29	PIO	2
PIO2	30	PIO	2
PIO2	iCE65L01: 34 iCE65L04: 36	PIO	2
PIO2	37	PIO	2
PIO2	40	PIO	2
PIO2/CBSEL0	41	PIO	2
PIO2/CBSEL1	42	PIO	2
VCCIO_2	31	VCCIO	2
VCCIO_2	38	VCCIO	2
PIO3/DP00A	1	PIO/DPIO	3
PIO3/DP00B	2	PIO/DPIO	3
PIO3/DP01A	3	PIO/DPIO	3
PIO3/DP01B	4	PIO/DPIO	3
PIO3/DP02A	7	PIO/DPIO	3
PIO3/DP02B	8	PIO/DPIO	3
PIO3/DP03A	9	PIO/DPIO	3
PIO3/DP03B	10	PIO/DPIO	3
PIO3/DP04A	12	PIO/DPIO	3
GBIN7/PIO3/DP04B	13	GBIN/DPIO	3
GBIN6/PIO3/DP05A	15	GBIN/DPIO	3
PIO3/DP05B	16	PIO/DPIO	3
PIO3/DP06A	18	PIO/DPIO	3
PIO3/DP06B	19	PIO/DPIO	3
PIO3/DP07A	20	PIO/DPIO	3
PIO3/DP07B	21	PIO/DPIO	3
PIO3/DP08A	24	PIO/DPIO	3
PIO3/DP08B	25	PIO/DPIO	3
VCCIO_3	6	VCCIO	3
VCCIO_3	14	VCCIO	3
VCCIO_3	22	VCCIO	3
PIOS/SPI_SO	45	SPI	SPI
PIOS/SPI_SI	46	SPI	SPI
PIOS/SPI_SCK	48	SPI	SPI
PIOS/SPI_SS_B	49	SPI	SPI
SPI_VCC	50	SPI	SPI
GND	5	GND	GND
GND	17	GND	GND
GND	23	GND	GND
GND	32	GND	GND
GND	39	GND	GND
GND	47	GND	GND
GND	55	GND	GND
GND	70	GND	GND
GND	84	GND	GND
GND	98	GND	GND
VCC	11	VCC	VCC
VCC	35	VCC	VCC

iCE65 Ultra Low-Power mobileFPGA™ Family

Ball Function	Ball Number	Pin Type	Bank
GND	K2	GND	GND
GND	K10	GND	GND
VCC	B6	VCC	VCC
VCC	F1	VCC	VCC
VCC	F11	VCC	VCC
VCC	K6	VCC	VCC
VPP_2V5	C10	VPP	VPP
VPP_FAST	A9	VPP	VPP

Ball Function	Ball Number	Pin Type	Bank
PIO2 (◆)	<i>ICE65L04:</i> N8 <i>ICE65L08:</i> L7	PIO	2
PIO2	N9	PIO	2
PIO2	N11	PIO	2
PIO2	N12	PIO	2
PIO2	N13	PIO	2
PIO2	P1	PIO	2
PIO2	P2	PIO	2
PIO2	P3	PIO	2
PIO2	P4	PIO	2
PIO2	P7	PIO	2
PIO2	P8	PIO	2
PIO2	P9	PIO	2
PIO2/CBSEL0	L9	PIO	2
PIO2/CBSEL1	P10	PIO	2
VCCIO_2	J9	VCCIO	2
VCCIO_2	M5	VCCIO	2
VCCIO_2	N10	VCCIO	2
PIO3/DP00A	C1	DPIO	3
PIO3/DP00B	B1	DPIO	3
PIO3/DP01A	D3	DPIO	3
PIO3/DP01B	C3	DPIO	3
PIO3/DP02A	D1	DPIO	3
PIO3/DP02B	D2	DPIO	3
PIO3/DP03A (◆)	<i>ICE65L04:</i> E1 <i>ICE65L08:</i> E2	DPIO	3
PIO3/DP03B (◆)	<i>ICE65L04:</i> E2 <i>ICE65L04:</i> E1	DPIO	3
PIO3/DP04A	D4	DPIO	3
PIO3/DP04B	E4	DPIO	3
PIO3/DP05A (◆)	<i>ICE65L04:</i> F3 <i>ICE65L08:</i> F4	DPIO	3
PIO3/DP05B (◆)	<i>ICE65L04:</i> F4 <i>ICE65L08:</i> F3	DPIO	3
PIO3/DP06A	F5	DPIO	3
PIO3/DP06B	E5	DPIO	3
PIO3/DP07A (◆)	<i>ICE65L04:</i> G2 <i>ICE65L08:</i> H4	DPIO	3
GBIN7/PIO3/DP07B (◆)	<i>ICE65L04:</i> G1 <i>ICE65L08:</i> H3	GBIN	3
GBIN6/PIO3/DP08A	H1	GBIN	3
PIO3/DP08B	H2	DPIO	3
PIO3/DP09A	G3	DPIO	3
PIO3/DP09B	G4	DPIO	3
PIO3/DP10A	J1	DPIO	3
PIO3/DP10B	J2	DPIO	3
PIO3/DP11A (◆)	<i>ICE65L04:</i> H4 <i>ICE65L08:</i> G1	DPIO	3
PIO3/DP11B (◆)	<i>ICE65L04:</i> H3 <i>ICE65L08:</i> G2	DPIO	3
PIO3/DP12A	K2	DPIO	3
PIO3/DP12B	J3	DPIO	3

iCE65 Ultra Low-Power mobileFPGA™ Family

Ball Function	Ball Number	Pin Type by Device		Bank	CB132 Ball Equivalent
	iCE65L04 iCE65L08	iCE65L04	iCE65L08		
VCCIO_3	J7	VCCIO	VCCIO	3	E3
VCCIO_3	K3	VCCIO	VCCIO	3	—
VCCIO_3	N10	VCCIO	VCCIO	3	J6
VCCIO_3	P5	VCCIO	VCCIO	3	K1
VCCIO_3	R3	VCCIO	VCCIO	3	—
VREF	M1	VREF	VREF	3	—
PIOS/SPI_SO	T15	SPI	SPI	SPI	M11
PIOS/SPI_SI	V15	SPI	SPI	SPI	P11
PIOS/SPI_SCK	V16	SPI	SPI	SPI	P12
PIOS/SPI_SS_B	V17	SPI	SPI	SPI	P13
SPI_VCC	R15	SPI	SPI	SPI	L11
GND	C12	GND	GND	GND	—
GND	E13	GND	GND	GND	A9
GND	J3	GND	GND	GND	—
GND	K5	GND	GND	GND	F1
GND	K11	GND	GND	GND	F7
GND	L11	GND	GND	GND	G7
GND	L12	GND	GND	GND	G8
GND	L13	GND	GND	GND	G9
GND	M10	GND	GND	GND	H6
GND	M11	GND	GND	GND	H7
GND	M12	GND	GND	GND	H8
GND	N1	GND	GND	GND	—
GND	N12	GND	GND	GND	J8
GND	N18	GND	GND	GND	J14
GND	N20	GND	GND	GND	—
GND	R7	GND	GND	GND	L3
GND	T3	GND	GND	GND	—
GND	V1	GND	GND	GND	—
GND	V10	GND	GND	GND	P6
GND	Y12	GND	GND	GND	—
GND	Y16	GND	GND	GND	—
GND	AB5	GND	GND	GND	—
GND	G1	GND	GND	GND	—
GND	R1	GND	GND	GND	—
VCC	C8	VCC	VCC	VCC	—
VCC	D3	VCC	VCC	VCC	—
VCC	K12	VCC	VCC	VCC	F8
VCC	L10	VCC	VCC	VCC	G6
VCC	L20	VCC	VCC	VCC	—
VCC	M13	VCC	VCC	VCC	H9
VCC	N8	VCC	VCC	VCC	J4
VCC	N11	VCC	VCC	VCC	J7
VCC	Y8	VCC	VCC	VCC	—
VPP_2V5	E18	VPP	VPP	VPP	A14
VPP_FAST	E17	VPP	VPP	VPP	A13

iCE65 Ultra Low-Power mobileFPGA™ Family

iCE65L08 Pad Name	Available Packages		DiePlus		
	CB196	CB284	Pad	X (μm)	Y (μm)
TDI	M12	T16	177	4,470.5	634.615
TMS	P14	V18	178	4,572.5	684.615
TCK	L12	R16	179	4,470.5	734.615
TDO	N14	U18	180	4,572.5	784.615
TRST_B	M14	T18	181	4,470.5	834.615
PIO1_00	M13	R18	182	4,572.5	884.615
PIO1_01	K11	P16	183	4,470.5	934.615
PIO1_02	L13	P15	184	4,572.5	984.615
PIO1_03	L14	P18	185	4,470.5	1,034.615
GND	G9	N18	186	4,572.5	1,084.615
GND	—	—	187	4,470.5	1,134.615
PIO1_04	J11	N16	188	4,572.5	1,184.615
PIO1_05	K12	N15	189	4,470.5	1,234.62
VCCIO_1	F9	M18	190	4,572.5	1,287.115
VCCIO_1	—	—	191	4,470.5	1,322.115
PIO1_06	J12	M15	192	4,572.5	1,357.115
PIO1_07	K14	M16	193	4,470.5	1,392.115
PIO1_08	—	T20	194	4,572.5	1,427.115
PIO1_09	—	W20	195	4,470.5	1,462.115
PIO1_10	—	V20	196	4,572.5	1,497.115
VCC	H9	M13	197	4,470.5	1,532.115
VCC	—	—	198	4,572.5	1,567.115
PIO1_11	—	R20	199	4,470.5	1,602.115
PIO1_12	—	Y22	200	4,572.5	1,637.115
PIO1_13	—	AA22	201	4,470.5	1,672.115
PIO1_14	—	U20	202	4,572.5	1,707.115
PIO1_15	J13	W22	203	4,470.5	1,742.115
PIO1_16	H11	P20	204	4,572.5	1,777.115
PIO1_17	J10	V22	205	4,470.5	1,812.115
PIO1_18	H12	U22	206	4,572.5	1,847.115
GND	K10	N20	207	4,470.5	1,882.115
GND	—	—	208	4,572.5	1,917.110
PIO1_19	H13	T22	209	4,470.5	1,952.115
PIO1_20	—	M20	210	4,572.5	1,987.115
PIO1_21	H10	R22	211	4,470.5	2,022.115
PIO1_22	—	P22	212	4,572.5	2,057.115
VCCIO_1	F9	J20	213	4,470.5	2,092.115
VCCIO_1	—	—	214	4,572.5	2,127.115
PIO1_23	G10	M22	215	4,470.5	2,162.115
PIO1_24	G11	N22	216	4,572.5	2,197.115
PIO1_25	—	K22	217	4,470.5	2,232.115
PIO1_26	—	L22	218	4,572.5	2,267.115
GBIN3/PIO1_27	G12	K18	219	4,470.5	2,302.11
GBIN2/PIO1_28	F10	L18	220	4,572.5	2,337.115
PIO1_29	—	J22	221	4,470.5	2,372.115

iCE65 Ultra Low-Power mobileFPGA™ Family

iCE65L08 Pad Name	Available Packages		DiePlus		
	CB196	CB284	Pad	X (μm)	Y (μm)
GND	F7	E13	270	3,216.98	4,054.5
GND	—	—	271	3,166.98	4,156.5
PIO0_08	D9	E15	272	3,116.98	4,054.5
PIO0_09	C10	G14	273	3,064.48	4,156.5
PIO0_10	A10	A20	274	3,029.48	4,054.5
PIO0_11	B10	H13	275	2,994.48	4,156.5
PIO0_12	—	A19	276	2,959.48	4,054.5
PIO0_13	E9	G13	277	2,924.48	4,156.5
PIO0_14	—	C16	278	2,889.48	4,054.5
PIO0_15	—	E14	279	2,854.48	4,156.5
VCCIO_0	F6	E12	280	2,819.48	4,054.5
VCCIO_0	—	—	281	2,784.48	4,156.5
PIO0_16	—	A18	282	2,749.48	4,054.5
PIO0_17	—	A17	283	2,714.48	4,156.5
PIO0_18	C9	C15	284	2,679.48	4,054.5
PIO0_19	—	A16	285	2,644.48	4,156.5
PIO0_20	B9	C14	286	2,609.48	4,054.5
PIO0_21	—	H12	287	2,574.48	4,156.5
PIO0_22	D8	A15	288	2,539.48	4,054.5
PIO0_23	C8	H11	289	2,504.48	4,156.5
PIO0_24	E8	C13	290	2,469.48	4,054.5
PIO0_25	—	A14	291	2,434.48	4,156.5
GND	B12	C12	292	2,399.48	4,054.5
GND	—	—	293	2,364.48	4,156.5
PIO0_26	B8	A13	294	2,329.48	4,054.5
PIO0_27	D7	A12	295	2,294.48	4,156.5
PIO0_28	—	C11	296	2,259.48	4,054.5
GBIN1/PIO0_29	E7	E11	297	2,224.48	4,156.5
GBIN0/PIO0_30	A7	E10	298	2,189.48	4,054.5
PIO0_31	—	G12	299	2,154.48	4,156.5
VCCIO_0	A8	A8	300	2,119.48	4,054.5
VCCIO_0	—	—	301	2,084.48	4,156.5
PIO0_32	C7	A11	302	2,049.48	4,054.5
PIO0_33	—	G11	303	2,014.48	4,156.5
PIO0_34	E6	A10	304	1,979.48	4,054.5
PIO0_35	—	C10	305	1,944.48	4,156.5
VCC	B7	C8	306	1,909.48	4,054.5
VCC	—	—	307	1,874.48	4,156.5
PIO0_36	—	A9	308	1,839.48	4,054.5
PIO0_37	A6	A7	309	1,804.48	4,156.5
PIO0_38	B6	C9	310	1,769.48	4,054.5
PIO0_39	A5	A6	311	1,734.48	4,156.5
GND	G7	K11	312	1,699.48	4,054.5
GND	—	—	313	1,664.48	4,156.5
PIO0_40	D6	E9	314	1,629.48	4,054.5
PIO0_41	C6	G10	315	1,594.48	4,156.5

iCE65L08 Pad Name	Available Packages		DiePlus		
	CB196	CB284	Pad	X (μm)	Y (μm)
PI00_42	C5	A5	316	1,559.48	4,054.5
PI00_43	B5	G9	317	1,524.48	4,156.5
PI00_44	A4	A3	318	1,489.48	4,054.5
PI00_45	—	A4	319	1,454.48	4,156.5
PI00_46	—	A2	320	1,419.48	4,054.5
PI00_47	—	C7	321	1,384.48	4,156.5
PI00_48	—	C6	322	1,331.98	4,054.5
VCCIO_0	A8	K10	323	1,281.98	4,156.5
VCCIO_0	—	—	324	1,231.98	4,054.5
PI00_49	—	E8	325	1,181.98	4,156.5
PI00_50	B4	A1	326	1,131.98	4,054.5
PI00_51	C4	E7	327	1,081.98	4,156.5
PI00_52	A3	C5	328	1,031.98	4,054.5
PI00_53	B3	E6	329	981.98	4,156.5
PI00_54	D5	C3	330	931.98	4,054.5
GND	A9	L11	331	881.98	4,156.5
GND	—	—	332	831.98	4,054.5
PI00_55	B2	G8	333	781.98	4,156.5
PI00_56	A2	C4	334	731.98	4,054.5
PI00_57	A1	H10	335	681.98	4,156.5
PI00_58	—	E5	336	631.98	4,054.5
PI00_59	—	H9	337	581.98	4,156.5

Electrical Characteristics

All parameter limits are specified under worst-case supply voltage, temperature, and processing conditions.

Absolute Maximum Ratings

Stresses beyond those listed under Table 47 may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions is not implied. Exposure to absolute maximum conditions for extended periods of time adversely affects device reliability.

Table 47: Absolute Maximum Ratings

Symbol	Description	Min	Max	Units
VCC	Core supply Voltage	−0.5	1.42	V
VPP_2V5	VPP_2V5 NVCM programming and operating supply			V
VPP_FAST	Optional fast NVCM programming supply			V
VCCIO_0 VCCIO_1 VCCIO_2 SPI_VCC	I/O bank supply voltage (I/O Banks 0, 1, and 2 plus SPI interface)	−0.5	4.00	V
VCCIO_3	I/O Bank 3 supply voltage	−0.5	iCE65L01: 4.00 iCE65L04/08: 3.6	V
VIN_0 VIN_1 VIN_2 VIN_SPI	Voltage applied to PIO pin within a specific I/O bank (I/O Banks 0, 1, and 2 plus SPI interface)	−1.0	5.5	V
VIN_3 VIN_VREF	Voltage applied to PIO pin within I/O Bank 3	−0.5	iCE65L01: 4.00 iCE65L04/08: 3.6	V
IOUT	DC output current per pin	—	20	mA
T_J	Junction temperature	−55	125	°C
T_{STG}	Storage temperature, no bias	−65	150	°C

Recommended Operating Conditions

Table 48: Recommended Operating Conditions

Symbol	Description		Minimum	Nominal	Maximum	Units
VCC	Core supply voltage	–L: Ultra-Low Power mode	0.95	1.00	1.05	V
		–L: Low Power	1.14	1.20	1.26	V
		–T: High Performance				
VPP_2V5	VPP_2V5 NVCM programming and operating supply	Release from Power-on Reset	1.30	—	3.47	V
		Configure from NVCM	2.30	—	3.47	V
		NVCM programming	2.30	—	3.00	V
VPP_FAST	Optional fast NVCM programming supply		Leave unconnected in application			
SPI_VCC	SPI interface supply voltage		1.71	—	3.47	V
VCCIO_0 VCCIO_1 VCCIO_2 VCCIO_3 SPI_VCC	I/O standards, all banks*	LVC MOS33	3.14	3.30	3.47	V
		Non-standard voltage: in between 2.5V and 3.3V use LVC MOS25 in iCEcube2	Nominal –5%	2.5< Nominal <3.3	Nominal +5%	V
		LVC MOS25, LVDS	2.38	2.50	2.63	V
		LVC MOS18, SubLVDS	1.71	1.80	1.89	V
		LVC MOS15	1.43	1.50	1.58	V
VCCIO_3	I/O standards only available in iCE65L04/08 I/O Bank 3*	SSTL2	2.38	2.50	2.63	V
		SSTL18	1.71	1.80	1.89	V
		MDDR	1.71	1.80	1.89	V
T _A	Ambient temperature	Commercial (C)	0	—	70	°C
		Industrial (I)	–40	—	85	°C
T _{PROG}	NVCM programming temperature		10	25	30	°C

NOTE:

VPP_FAST is only used for fast production programming. Leave floating or unconnected in application. When the iCE65 device is active, VPP_2V5 must be connected to a valid voltage.

I/O Characteristics

Table 49: PIO Pin Electrical Characteristics

Symbol	Description	Conditions	Minimum	Nominal	Maximum	Units
I_I	Input pin leakage current	I/O Bank 0, 1, 2 $V_{IN} = V_{CCIO_{max}}$ to 0 V			± 10	μA
		I/O Bank 3 $V_{IN} = V_{CCIO_{max}}$				
I_{OZ}	Three-state I/O pin (Hi-Z) leakage current	$V_O = V_{CCIO_{max}}$ to 0 V			± 10	μA
C_{PIO}	PIO pin input capacitance			6		pF
C_{GBIN}	GBIN global buffer pin input capacitance			6		pF
R_{PULLUP}	Internal PIO pull-up resistance during configuration	$V_{CCIO} = 3.3V$		40		k Ω
		$V_{CCIO} = 2.5V$		50		k Ω
		$V_{CCIO} = 1.8V$		90		k Ω
		$V_{CCIO} = 1.5V$				k Ω
		$V_{CCIO} = 1.2V$				k Ω
V_{HYST}	Input hysteresis	$V_{CCIO} = 1.5V$ to 3.3V		50		mV

NOTE: All characteristics are characterized and may or may not be tested on each pin on each device.

Single-ended I/O Characteristics

Table 50: I/O Characteristics (I/O Banks 0, 1, 2 and SPI only) (I/O Bank 3 iCE65L01 only)

I/O Standard	Nominal I/O Bank Supply Voltage	Input Voltage (V)		Output Voltage (V)		Output Current at Voltage (mA)	
		V_{IL}	V_{IH}	V_{OL}	V_{OH}	I_{OL}	I_{OH}
LVC MOS33	3.3V	0.80	2.00	0.4	2.40	8	8
LVC MOS25	2.5V	0.70	1.70	0.4	2.00	6	6
LVC MOS18	1.8V	35% VCCIO	65% VCCIO	0.4	1.40	4	4
LVC MOS15	1.5V	Not supported Use I/O Bank 3		0.4	1.20	2	2

Table 51: I/O Characteristics (I/O Bank 3 and iCE65L04/08 only)

I/O Standard	Supply Voltage	Input Voltage (V)		Output Voltage (V)		I/O Attribute Name	mA at Voltage
		Max. V_{IL}	Min. V_{IH}	Max. V_{OL}	Min. V_{OH}		I_{OL} , I_{OH}
LVC MOS33	3.3V	0.80	2.20	0.4	2.40	SL_LVC MOS33_8	± 8
LVC MOS25	2.5V	0.70	1.70	0.4	2.00	SB_LVC MOS25_16	± 16
						SB_LVC MOS25_12	± 12
						SB_LVC MOS25_8 *	± 8
						SB_LVC MOS25_4	± 4
LVC MOS18	1.8V	35% VCCIO	65% VCCIO	0.4	VCCIO-0.45	SB_LVC MOS18_10	± 10
						SB_LVC MOS18_8	± 8
						SB_LVC MOS18_4 *	± 4
						SB_LVC MOS18_2	± 2
LVC MOS15	1.5V	35% VCCIO	65% VCCIO	25% VCCIO	75% VCCIO	SB_LVC MOS15_4	± 4
						SB_LVC MOS15_2 *	± 2
MDDR	1.8V	35% VCCIO	65% VCCIO	0.4	VCCIO-0.45	SB_MDDR10	± 10
						SB_MDDR8	± 8
						SB_MDDR4 *	± 4
						SB_MDDR2	± 2
SSTL2 (Class 2)	2.5V	VREF-0.180	VREF+0.180	0.35	VTT+0.430	SB_SSTL2_CLASS_2	± 16.2
SSTL2 (Class 1)				0.54		SB_SSTL2_CLASS_1	± 8.1
SSTL18 (Full)	1.8V	VREF-0.125	VREF+0.125	0.28	VTT+0.280	SB_SSTL18_FULL	± 13.4
SSTL18 (Half)				VTT-0.475	VTT+0.475	SB_SSTL18_HALF	± 6.7

NOTES:

SSTL2 and SSTL18 I/O standards require the VREF input pin, which is only available on the CB284 package and die-based products.

I/O Banks 0, 1, 2 and SPI Bank Characteristic Curves

Figure 52: Typical LVC MOS Output Low Characteristics (I/O Banks 0, 1, 2, and SPI)

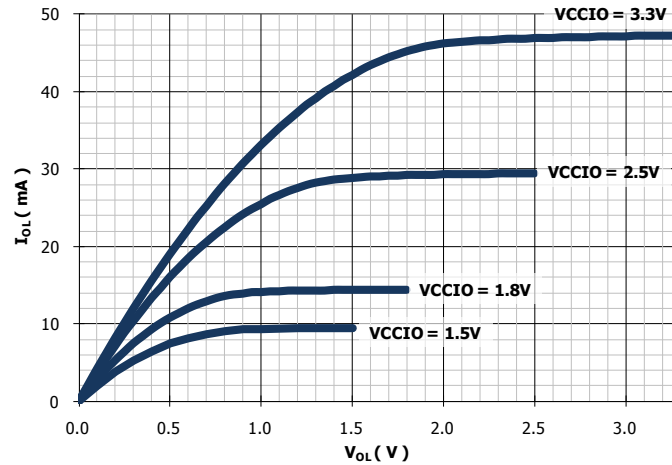


Figure 53: Typical LVC MOS Output High Characteristics (I/O Banks 0, 1, 2, and SPI)

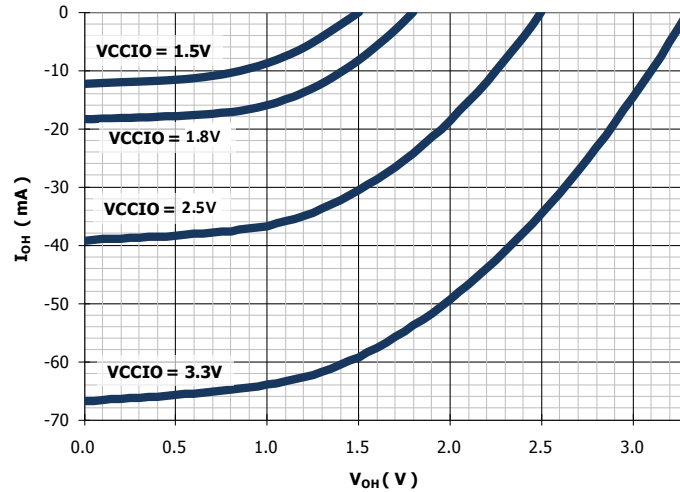
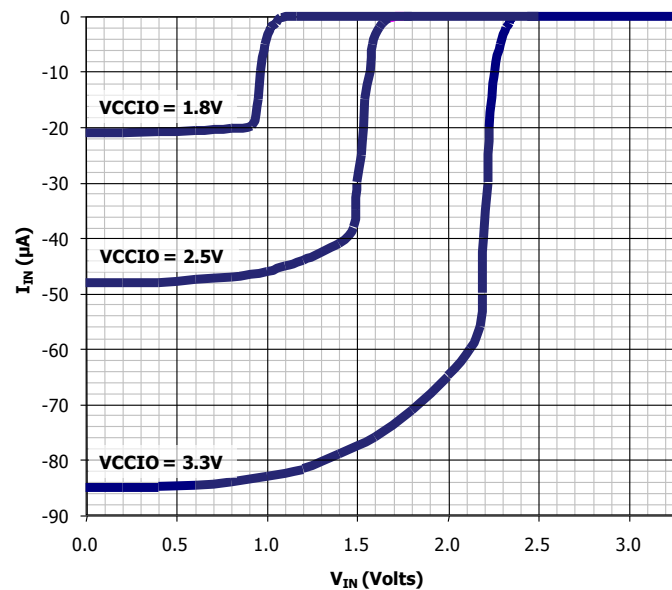


Figure 54: Input with Internal Pull-Up Resistor Enabled (I/O Banks 0, 1, 2, and SPI)



Programmable Input/Output (PIO) Block

Table 55 provides timing information for the logic in a Programmable Logic Block (PLB), which includes the paths shown in Figure 57 and Figure 58. The timing shown is for the LVCMOS25 I/O standard in all I/O banks. The iCEcube development software reports timing adjustments for other I/O standards.

Figure 57: Programmable I/O (PIO) Pad-to-Pad Timing Circuit

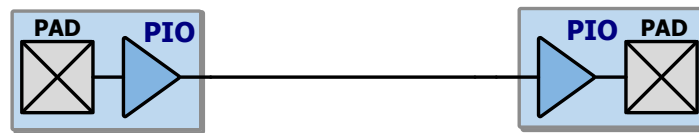


Figure 58: Programmable I/O (PIO) Sequential Timing Circuit

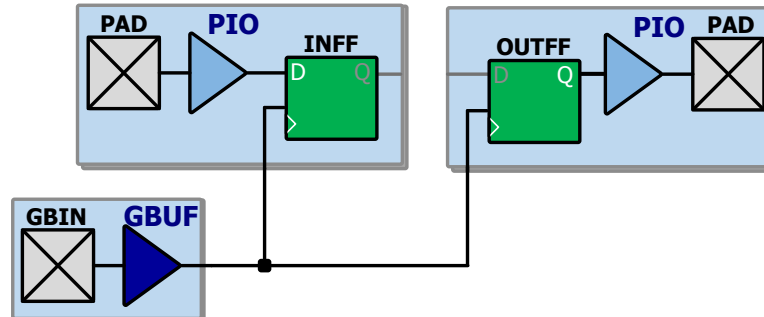


Table 55: Typical Programmable Input/Output (PIO) Timing (LVCMOS25)

Symbol	From	To	Device: iCE65	L01	L04, L08			Units
			Power/Speed Grad	−T	−L		−T	
			Nominal VCC	1.2 V	1.0 V	1.2 V	1.2 V	
			Description	Typ.	Typ.	Typ.	Typ.	
Synchronous Output Paths								
t _{OCKO}	OUTFF clock input	PIO output	Delay from clock input on OUTFF output flip-flop to PIO output pad.	4.7	13.8	7.3	5.6	ns
t _{GBCKIO}	GBIN input	OUTFF clock input	Global Buffer Input (GBIN) delay, though Global Buffer (GBUF) clock network to clock input on the PIO OUTFF output flip-flop.	2.1	7.3	3.8	2.6	ns
Synchronous Input Paths								
t _{SUPDIN}	PIO input	GBIN input	Setup time on PIO input pin to INFF input flip-flop before active clock edge on GBIN input, including interconnect delay.	0	0	0	0	ns
t _{HDPDIN}	GBIN input	PIO input	Hold time on PIO input to INFF input flip-flop after active clock edge on the GBIN input, including interconnect delay.	2.7	7.1	3.6	2.8	ns
Pad to Pad								
t _{PADIN}	PIO input	Inter-connect	Asynchronous delay from PIO input pad to adjacent interconnect.	2.5	9.5	5.0	3.2	ns
t _{PADO}	Inter-connect	PIO output	Asynchronous delay from adjacent interconnect to PIO output pad including interconnect delay.	4.5	14.6	7.7	6.2	ns

Internal Configuration Oscillator Frequency

Table 57 shows the operating frequency for the iCE65's internal configuration oscillator.

Table 57: Internal Oscillator Frequency

Symbol	Oscillator Mode	Frequency (MHz)		Description
		Min.	Max.	
f_{OSCD}	Default	4.0	6.8	Default oscillator frequency. Slow enough to safely operate with any SPI serial PROM.
f_{OSCL}	Low Frequency	14	21	Supported by most SPI serial Flash PROMs
f_{OSCH}	High Frequency	21	31	Supported by some high-speed SPI serial Flash PROMs
	Off	0	0	Oscillator turned off by default after configuration to save power.

Configuration Timing

Table 58 shows the maximum time to configure an iCE65 device, by oscillator mode. The calculations use the slowest frequency for a given oscillator mode from Table 57 and the maximum configuration bitstream size from Table 1 which includes full RAM4K block initialization. The configuration bitstream selects the desired oscillator mode based on the performance of the configuration data source.

Table 58: Maximum SPI Master or NVCM Configuration Timing by Oscillator Mode

Symbol	Description	Device	Default	Low Freq.	High Freq.	Units
$t_{CONFIGL}$	Time from when minimum Power-on Reset (POR) threshold is reached until user application starts.	iCE65L01	53	25	11	ms
		iCE65L04	115	55	25	ms
		iCE65L08	230	110	50	ms

Table 59 provides timing for the CRESET_B and CDONE pins.

Table 59: General Configuration Timing

Symbol	From	To	Description	All Grades		Units	
				Min.	Max.		
tCRESET_B	CRESET_B	CRESET_B	Minimum CRESET_B Low pulse width required to restart configuration, from falling edge to rising edge	200	—	ns	
tDONE_IO	CDONE High	PIO pins active	Number of configuration clock cycles after CDONE goes High before the PIO pins are activated.	—	49	Clock cycles	
			SPI Peripheral Mode (Clock = SPI_SCK, cycles measured rising-edge to rising-edge)	Depends on SPI_SCK frequency			
			NVCM or SPI Master Mode by internal oscillator frequency setting (Clock = internal oscillator)	Default	7.20	12.25	μs
				Low	2.34	3.50	μs
				High	1.59	2.33	μs